In the Abstract:

Please rewrite the abstract as follows:

Semiconductor substrate and semiconductor circuit formed therein and associated fabrication methods

The invention relates to aA semiconductor substrate and to-a semiconductor circuit formed therein and associated fabrication methods, are provided. a-A multiplicity of depressions (P) with a respective dielectric layer (D) and a capacitor electrode (E2) being are formed for realizing buried capacitors in a carrier substrate (1) and an actual semiconductor component layer (3) being insulated from the carrier substrate (1) by an insulation layer (2).

(Figure 1D)